

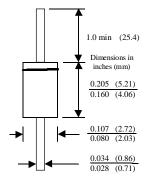
# Discrete POWER & Signal Technologies

### 1N5817 - 1N5819

#### **Features**

- 1.0 ampere operation at T<sub>A</sub> = 90°C with no thermal runaway.
- For use in low voltage, high frequency inverters free wheeling, and polarity protection applications.





## 1.0 Ampere Schottky Barrier Rectifiers

#### **Absolute Maximum Ratings\***

T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
Io	Average Rectified Current .375 " lead length @ T <sub>A</sub> = 90°C	1.0	Α
İf(surge)	Peak Forward Surge Current 8.3 ms single half-sine-wave Superimposed on rated load (JEDEC method)	25	А
P <sub>D</sub>	Total Device Dissipation  Derate above 25°C	1.25 12.5	W mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	80	°C/W
T <sub>stg</sub>	Storage Temperature Range	-65 to +125	°C
TJ	Operating Junction Temperature	-65 to +125	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### **Electrical Characteristics**

T<sub>A</sub> = 25°C unless otherwise noted

Parameter		Device			Units
		1N5817	1N5818	1N5819	
Peak Repetitive Reverse Volta	20	30	40	V	
Maximum RMS Voltage	14	21	28	V	
DC Reverse Voltage (Rated V <sub>R</sub> )		20	30	40	V
Maximum Reverse Current $T_A = 25^{\circ}\text{C}$ @ rated $V_R$ $T_A = 100^{\circ}\text{C}$			0.5 10		mA mA
Maximum Forward Voltage	@ 1.0 A @ 3.0 A	450 750	550 875	600 900	mV mV
Typical Junction Capacitance $V_R = 4.0 \text{ V}, f = 1.0 \text{ MHz}$		110		pF	

#### **Schottky Barrier Rectifiers**

(continued)

#### **Typical Characteristics**

